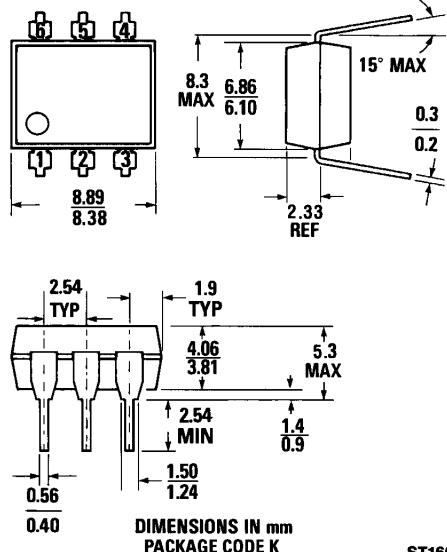




PHOTOTRANSISTOR OPTOCOUPLES

4N35 4N36 4N37

PACKAGE DIMENSIONS

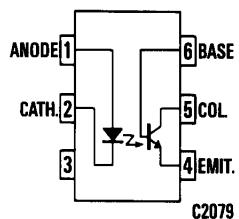


DESCRIPTION

The 4N35, 4N36, and 4N37 series of optocouplers have an NPN silicon planar phototransistor optically coupled to a gallium arsenide infrared emitting diode.

FEATURES & APPLICATIONS

- AC line/digital logic isolator
- Digital logic/digital logic isolator
- Telephone/telegraph line receiver
- Twisted pair line receiver
- High frequency power supply feedback control
- Relay contact monitor
- Power supply monitor
- Industrial controls
- Covered under UL component recognition program, reference File E90700
- High DC current transfer ratio



Equivalent Circuit

ABSOLUTE MAXIMUM RATINGS

TOTAL PACKAGE

- *Relative humidity 85% @ 85°C
- *Storage temperature -55°C to 150°C
- *Operating temperature -55°C to 100°C
- *Lead temperature (soldering, 10 sec) 260°C

INPUT DIODE

- *Forward DC current (continuous) 60 mA
- Reverse voltage 6 volts
- *Peak forward current
(1 μs pulse, 300 pps) 3.0 A
- *Power dissipation at $T_A=25^\circ\text{C}$ 100 mW \dagger
- *Power dissipation at $T_c=25^\circ\text{C}$ 100 mW \ddagger
(T_c indicates collector lead temp
1/32" from case)

OUTPUT TRANSISTOR

- *Power dissipation at 25°C ambient 300 mW
- Derate linearly above 25°C 4 mW/°C
- *Power dissipation at $T_c=25^\circ\text{C}$ 500 mW \ddagger
(T_c indicates collector lead temp
1/32" from case)

- * V_{CEO} 30 volts
- * V_{CBO} 70 volts
- * V_{ECO} 7 volts
- *Collector current (continuous) 100 mA

*Indicates JEDEC registered values

\dagger Derate 1.33 mW/°C above 25°C.

\ddagger Derate 6.7 mW/°C above 25°C.



PHOTOTRANSISTOR OPTOCOUPLES

ELECTRO-OPTICAL CHARACTERISTICS (25°C Free Air Temperature Unless Otherwise Specified)

INDIVIDUAL COMPONENT CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE						
*Forward voltage	V _F	.8		1.50	V	I _F =10 mA
*Forward voltage temp. coefficient	V _F	.9		1.7	V	I _F =10 mA, T _A =-55°C
*Forward voltage	V _F	.7		1.4	V	I _F =10 mA, T _A =+100°C
*Junction capacitance	C _J			100	pF	V _F =0 V, f=1 mHz
*Reverse leakage current			.01	10	μA	V _R =6.0 V
DETECTOR						
DC forward current gain	h _{FE}		250			V _{CE} =5 V, I _C =100 μA
*Collector to emitter breakdown voltage	BV _{CEO}	30	65		V	I _C =10 mA, I _F =0
*Collector to base breakdown voltage	BV _{CBO}	70	165		V	I _C =100 μA, I _F =0
*Emitter to collector breakdown voltage	BV _{ECD}	7	14		V	I _E =100 μA, I _F =0
Collector to emitter, leakage current	I _{CEO}		5	50	nA	V _{CE} =10 V, I _F =0
*Collector to emitter leakage current (dark)	I _{CEO}			500	μA	V _{CE} =30 V, I _F =0, T _A =100°C
Capacitance collector to emitter	C _{CEW}		8		pF	V _{CE} =0
Capacitance collector to base	C _{CBO}		20		pF	V _{CB} =10 V
Capacitance base to emitter	C _{BEO}		10		pF	V _{BE} =0

TRANSFER CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
COUPLED						
†*DC current transfer ratio	CTR	100			%	I _F =10 mA, V _{CE} =10 V
†*DC current transfer ratio	CTR	40			%	I _F =10 mA, V _{CE} =10 V, T _A =-55°C
†*DC current transfer ratio	CTR	40			%	I _F =10 mA, V _{CE} =10 V, T _A =+100°C
*Saturation voltage—collector to emitter	V _{CE(SAT)}			.3	volts	I _F =10 mA, I _C =0.5 mA

TRANSFER CHARACTERISTICS

AC CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
*Turn on time	t _{ON}		5	10	μsec	V _{CC} =10 V, I _C =2 mA, R _L =100Ω, (Fig. 10 and Fig. 11)
*Turn off time	t _{OFF}		5	10	μsec	V _{CC} =10 V, I _C =2 mA, R _L =100Ω, (Fig. 10 and Fig. 11)

*Indicates JEDEC registered values

†Pulse test: pulse width=300μS,
duty cycle≤2.0%



PHOTOTRANSISTOR OPTOCOUPERS

ELECTRO-OPTICAL CHARACTERISTICS

(25°C Free Air Temperature Unless Otherwise Specified) (Cont'd)

ISOLATION CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Isolation voltage all devices	V_{iso}	5300			V_{rms}	$I_{io} \leq 1\mu A$ $t=1$ minute
*Input to output isolation current (pulse width=8 msec) (see Note 1)	I_{io}					
4N35			100		μA	$V_{iso}=3550$ VAC (peak)
4N36			100		μA	$V_{iso}=2500$ VAC (peak)
4N37			100		μA	$V_{iso}=1500$ VAC (peak)
*Input to output resistance	R_{io}	100			gigaohms	Input to output voltage=500 V (see Note 1)
*Input to output capacitance	C_{io}		2.5		picofarads	Input to output voltage=0 V, $f=1$ MHz (see Note 1)

*Indicates JEDEC registered values

†Pulse test: pulse width=300μS,
duty cycle≤2.0%

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES

(25°C Free Air Temperature Unless Otherwise Specified)

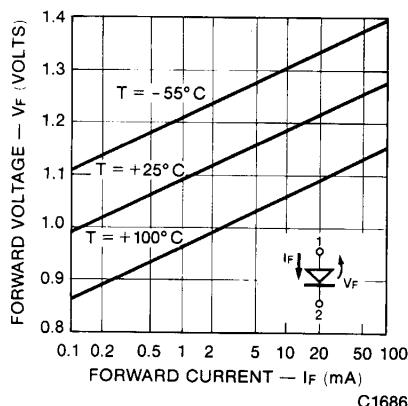


Fig. 1. Forward Voltage vs.
Current

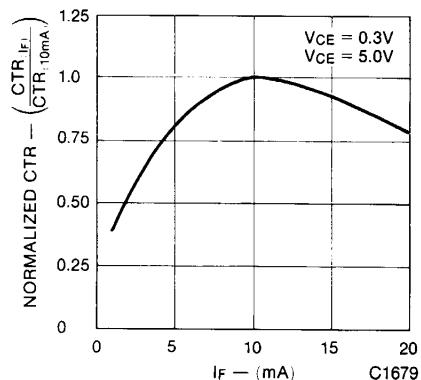
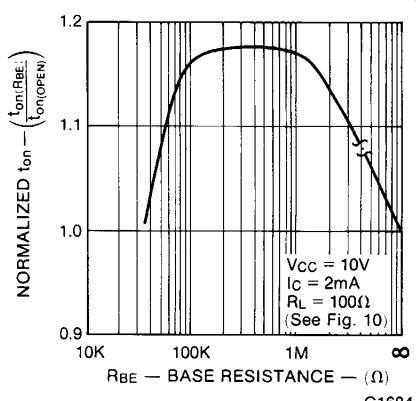
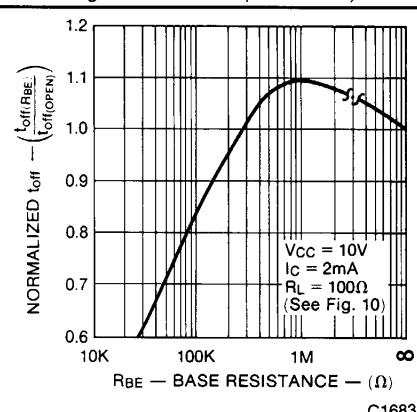
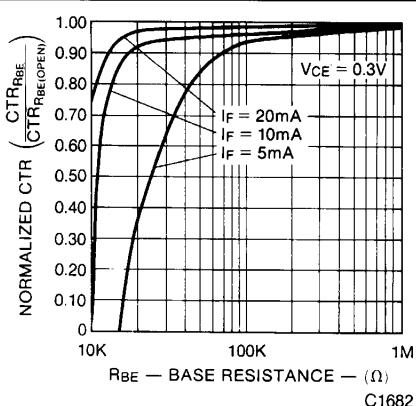
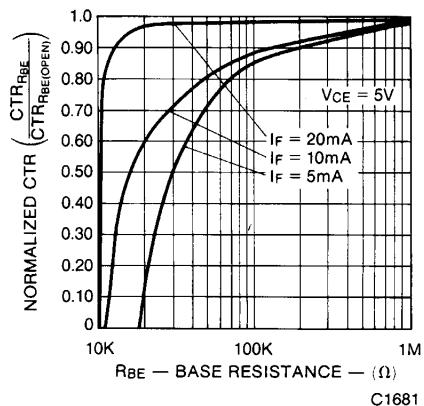
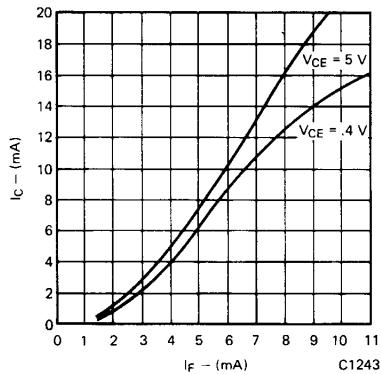
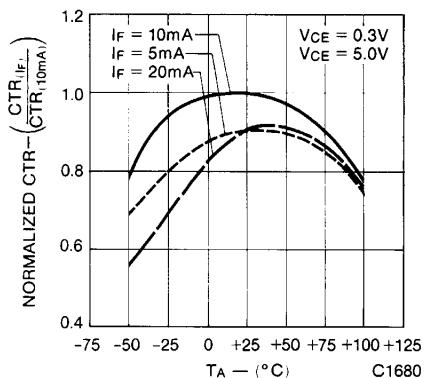


Fig. 2. Normalized CTR vs.
Forward Current

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES
(25°C Free Air Temperature Unless Otherwise Specified) (Cont'd)





PHOTOTRANSISTOR OPTOCOUPLES

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES (25°C Free Air Temperature Unless Otherwise Specified) (Cont'd)

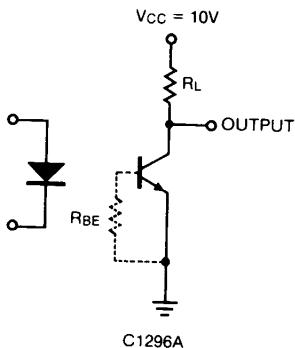
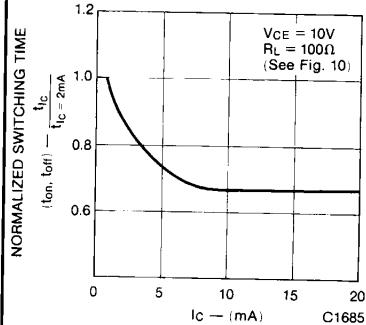


Fig. 10. Switching Time Test Circuit

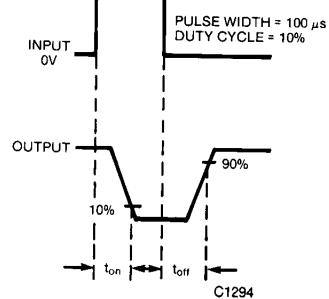


Fig. 11. Switching Time Waveforms

NOTES

1. Tests of input to output isolation current resistance and capacitance are performed with the input terminals (diode) shorted together and the output terminals (transistor) shorted together.
2. The current transfer ratio (I_C/I_F) is the ratio of the detector collector current to the LED input current with V_{CE} at 10 volts.
3. Rise time (t_r) is the time required for the collector current to increase from 10% of its final value, to 90%. Fall time (t_f) is the time required for the collector current to decrease from 90% of its initial value to 10%.

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Datasheets for electronics components.